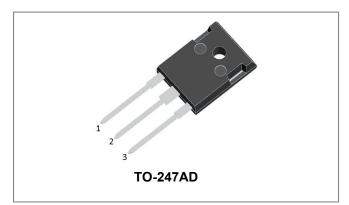


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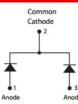
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Circuit Diagram



Features

- 150 °C T_J operation
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Terminals finish: Tin Lead-free plated
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection
 Conter top configuration
- Center tap configuration

Maximum Ratings(Tc=25 °C unless otherwise specified)

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	150	V
Average Rectified Forward Current	I _{F (AV)}	Tc=140°C, In DC	20(Per Leg) 40(Per Device)	А
Peak Repetitive Forward Current(Per Leg)	IFRM	Rated VR square wave, 20KHz Tc =135℃	20	А
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I _{FSM}	8.3ms, Half Sine pulse	250	А

Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop	V _{F1}	@ 20A, Pulse, T _J = 25℃	0.84	0.95	V
(Per Leg)*	V _{F2}	@ 20A, Pulse, TJ = 125℃	0.72	0.92	V
Reverse Current (Per Leg)*	I _{R1}	@V _R = rated V _R , T _J = 25°C	0.0005	1.0	mA
	I _{R2}	@V _R = rated V _R , T _J = 125 $^{\circ}$ C	0.1	6.0	mA
Junction Capacitance(Per Leg)	Ст	@V _R = 5V, T _C = 25℃	490	760	pF
		f _{sig} = 1MHz			
Series Inductance(Per Leg)	Ls	Measured lead to lead 5 mm	8.0	-	nH
		from package body			
Voltage Rate of Change	dv/dt	-	-	10,000	V/µs

* Pulse width < 300 μ s, duty cycle < 2%

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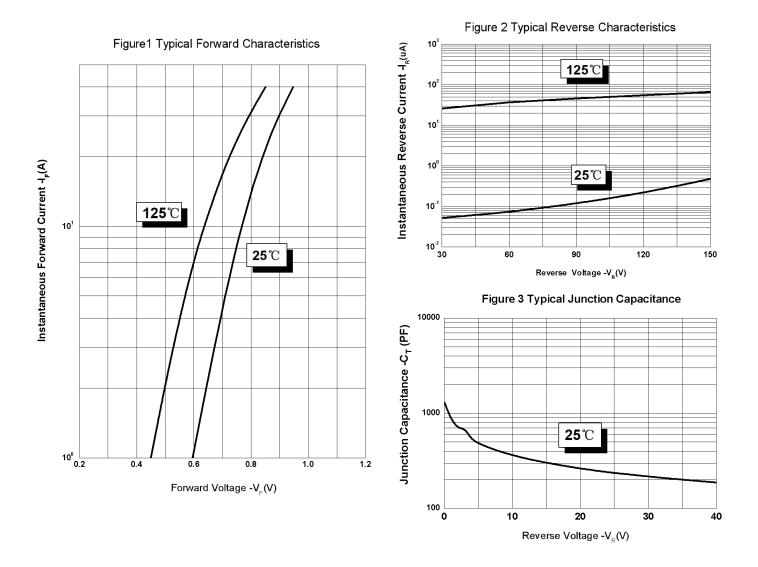
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Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T _{stg}	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case	$R_{ ext{ heta}JC}$	DC operation	0.5	°C/W
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

Ratings and Characteristics Curves







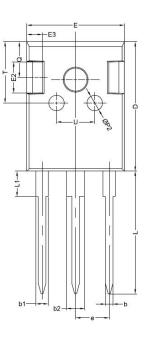
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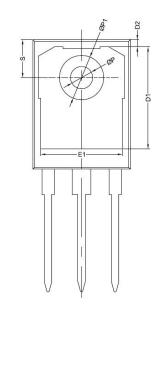
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Mechanical Dimensions TO-247AD

A1-





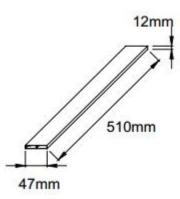
SYMBOL	Millimeters				
SYMBOL	MIN.	TYP.	MAX.		
А	4.80	5.00	5.20		
A1	2.20	2.41	2.61		
A2	1.90	2.00	2.10		
b	1.10	1.20	1.40		
b1	1.80	2.00	2.20		
b2	2.80	3.00	3.20		
С	0.50	0.60	0.75		
D	20.30	21.00	21.20		
D1		16.55			
D2		1.20			
E	15.45	15.80	16.00		
E1		13.30			
E2		5.00			
E3		2.50			
е		5.44			
L	19.42	19.92	20.70		
L1		4.13			
Р	3.50	3.60	3.70		
P1	7.1		7.40		
P2		2.50			
Q		5.80			
Q S	6.05	6.15	6.25		
Т		10.00			
U		6.20			

пп

Ordering Information:

Device	Package	Shipping	
MBR40150WT	TO-247AD(Pb-Free)	25pcs / tube	

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

- = Device Type = Forward Current (40A) MBR
 - = Reverse Voltage (150V)
 - = Configuration
 - = SSG
 - = Year = Week

40

150

WΤ

SSG

YΥ

ww

L

= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

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